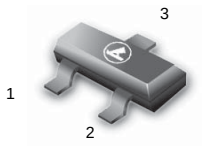
High Voltage Transistor

FEATURE

- We declare that the material of product compliance with RoHS requirements.

LMBT5401LT1G



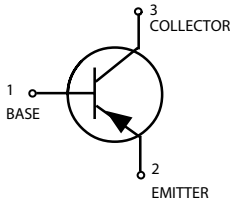
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DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBT5401LT1G	2L	3000/Tape&Reel
LMBT5401LT3G	2L	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	– 150	Vdc
Collector–Base Voltage	V_{CBO}	– 160	Vdc
Emitter–Base Voltage	V_{EBO}	– 5.0	Vdc
Collector Current — Continuous	I_C	– 500	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board (1) T_A=25 °C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T_A = 25°C	P_D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55to+150	°C

DEVICE MARKING

LMBT5401LT1G=2L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I_C = –1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	– 150	—	Vdc
Collector–Base Breakdown Voltage (I_C = –100 µAdc, I_E = 0)	$V_{(BR)CBO}$	– 160	—	Vdc
Emitter-BAse Breakdown Voltage (I_E= –10µAdc,I_C=0)	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current (V_{CB} = –120 Vdc, I_E= 0)	I_{CBO}	—	– 50	nAdc
(V_{CB} = –120 Vdc, I_E= 0, T_A=100 °C)		—	– 50	µAdc

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS (2)				
DC Current Gain	h_{FE}			—
(I_C = –1.0mAdc, V_{CE} = –5.0 Vdc)		50	—	
(I_C = –10 mAdc, V_{CE} = –5.0 Vdc)		60	240	
(I_C = –50 mAdc, V_{CE} = –5.0 Vdc)		50	—	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc
(I_C = –10 mAdc, I_B = –1.0 mAdc)		—	– 0.2	
(I_C = –50 mAdc, I_B = –5.0 mAdc)		—	– 0.5	
Base–Emitter Saturation Voltage	$V_{BE(sat)}$			Vdc
(I_C = –10 mAdc, I_B = –1.0 mAdc)		—	– 1.0	
(I_C = –50 mAdc, I_B = –5.0 mAdc)		—	– 1.0	
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product	f_T			MHz
(I_C = –10 mAdc, V_{CE}= –10 Vdc, f = 100 MHz)		100	300	
Output Capacitance	C_{obo}			pF
(V_{CB}= –10 Vdc, I_E = 0, f = 1.0 MHz)		—	6.0	
Small–Signal Current Gain	h_{fe}			—
(I_C= –1.0mAdc, V_{CE} = –10Vdc, f = 1.0 kHz)		40	200	
Noise Figure	NF			dB
(I_C = –200 μAdc, V_{CE}= –5.0 Vdc,R_S=10Ω, f = 1.0 kHz)		—	8.0	

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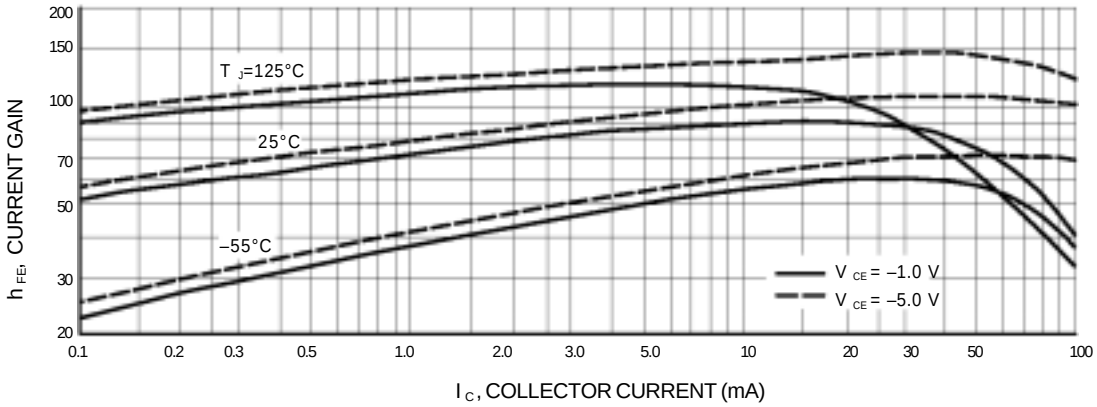


Figure 1. DC Current Gain

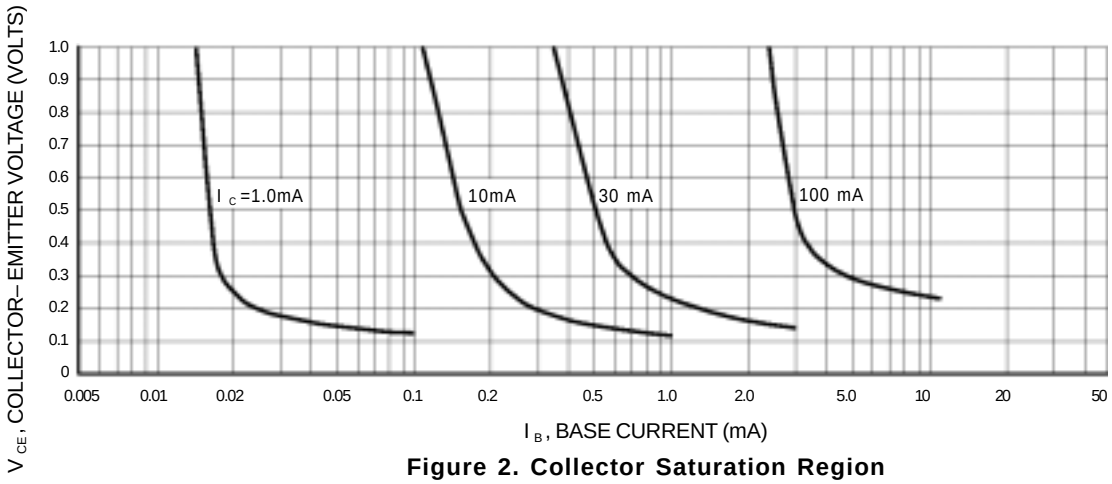


Figure 2. Collector Saturation Region

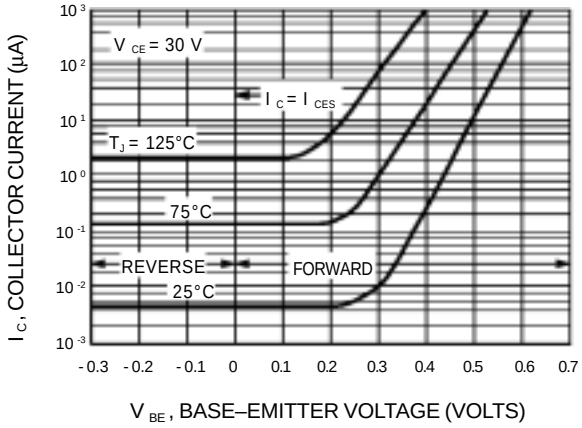


Figure 3. Collector Cut–Off Region

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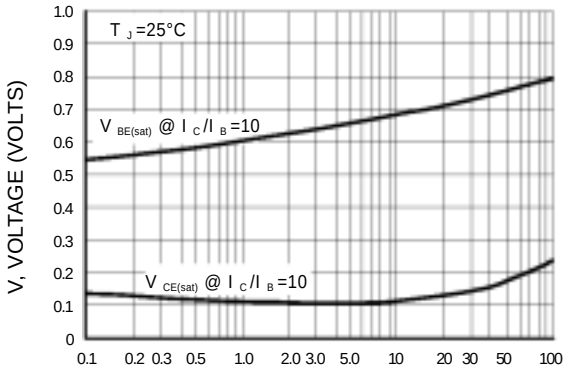


Figure 4. "On" Voltages

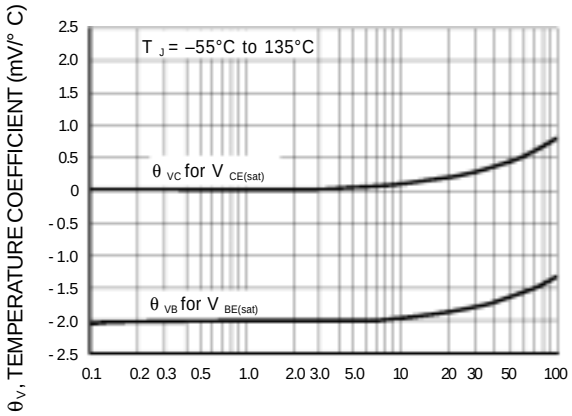


Figure 5. Temperature Coefficients

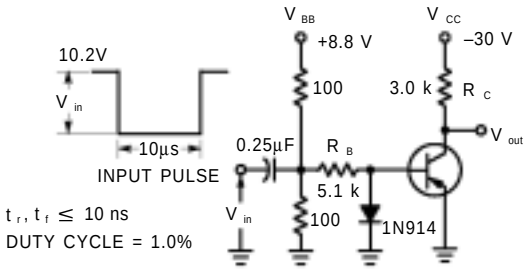


Figure 6. Switching Time Test Circuit

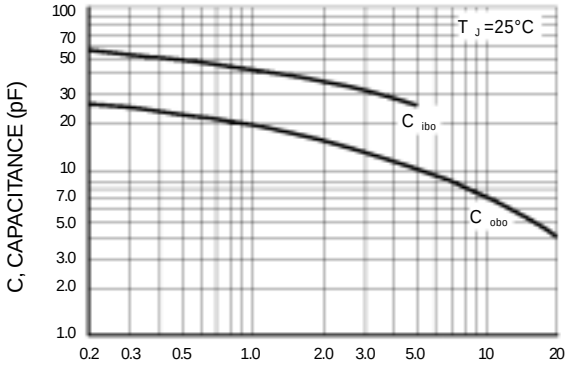


Figure 7. Capacitances

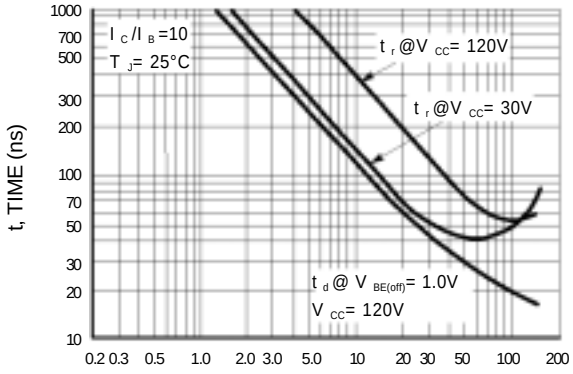


Figure 8. Turn–On Time

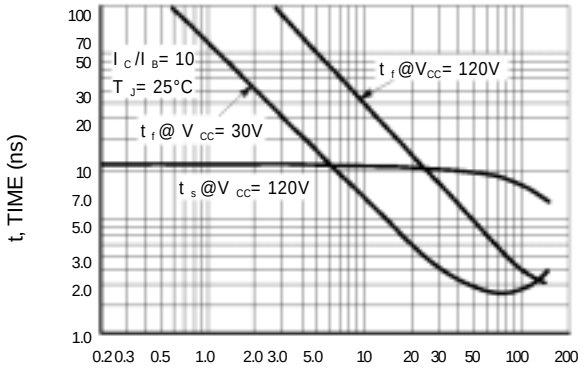
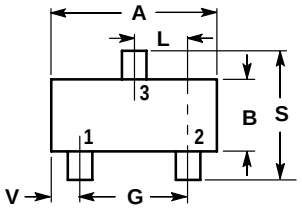
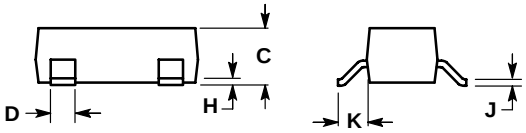


Figure 9. Turn–Off Time

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1. BASE
2. EMITTER
3. COLLECTOR

